High Power Dual Path Simultaneous DP3T Switch with Control Logic

CXM3544XR

Description

The CXM3544XR can be used in wireless communication systems, for example, dual-band/triple-band and antenna diversity CDMA handsets. This CXM3544XR has an integrated decoder 4 CMOS control inputs. The Sony JPHEMT process is used for low insertion loss and low distortion characteristic. (Applications: Antenna Switch for Cellular Handsets, Dual-band/Triple-band and Antenna Diversity)

Features

- ◆ Low insertion loss: 0.30dB (Typ.) @900MHz, 0.4dB (Typ.) @2GHz
- ♦ High linearity: IIP3 = 65dBm (Min.)
- ◆ Low voltage operation: VDD = 2.5V
- No DC blocking capacitors
- ◆ 4 CMOS compatible control line
- ◆ Lead-Free and RoHS compliant

Package

Small package XQFN 22pin (2.4mm × 3.3mm × 0.35mm) (Typ.)

Structure

GaAs JPHEMT MMIC, CMOS Logic

Absolute Maximum Ratings

 Bias voltage 	Vdd	4	V	(Ta = 25℃)
 Control voltage 	Vctl	4	V	(Ta = 25°C)
 Operating temperature 	Topr	-35 to +90	°C	
 Storage temperature 	Tstg	–65 to +150	°C	

This IC is ESD sensitive device. Special handling precautions are required.

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Block Diagram



Pin Configuration



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Truth Table

State	CTLA	CTLB	CTLC	CTLD	RF5 (Ant1)	RF4 (Ant2)	F1	F2	F3	F4	F5	F6	F7	F8	F9	F10	F11
1	Н	L	L	L	RF1	OFF	ON	OFF	OFF	OFF	OFF	OFF	OFF	ON	ON	OFF	ON
2	L	Н	L	L	RF2	OFF	OFF	ON	OFF	OFF	OFF	OFF	ON	OFF	ON	OFF	ON
3	L	L	L	L	RF3	OFF	OFF	OFF	ON	OFF	OFF	OFF	ON	ON	OFF	OFF	ON
4	Н	L	Н	L	OFF	RF1	OFF	OFF	OFF	ON	OFF	OFF	OFF	ON	ON	ON	OFF
5	L	Н	Н	L	OFF	RF2	OFF	OFF	OFF	OFF	ON	OFF	ON	OFF	ON	ON	OFF
6	L	L	Н	L	OFF	RF3	OFF	OFF	OFF	OFF	OFF	ON	ON	ON	OFF	ON	OFF
7	Н	Н	L	Н	RF1	RF2	ON	OFF	OFF	OFF	ON	OFF	OFF	OFF	ON	OFF	OFF
8	Н	L	L	Н	RF1	RF3	ON	OFF	OFF	OFF	OFF	ON	OFF	ON	OFF	OFF	OFF
9	Н	Н	Н	н	RF2	RF1	OFF	ON	OFF	ON	OFF	OFF	OFF	OFF	ON	OFF	OFF
10	L	Н	L	Н	RF2	RF3	OFF	ON	OFF	OFF	OFF	ON	ON	OFF	OFF	OFF	OFF
11	Н	L	Н	Н	RF3	RF1	OFF	OFF	ON	ON	OFF	OFF	OFF	ON	OFF	OFF	OFF
12	L	L	L	Н	RF3	RF2	OFF	OFF	ON	OFF	ON	OFF	ON	OFF	OFF	OFF	OFF

DC Bias Condition

(Ta = -35 to +90°C)

Item	Min.	Тур.	Max.	Unit
Vctl (H)	1.3	1.8	3.2	
Vctl (L)	0	—	0.3	V
Vdd	2.5	2.8	3.2	

Electrical Characteristics 1

(Ta = +25°C, V_{DD} = 2.8V, Vctl = 0/1.8V)

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
Control current	lctl	Vctl = 1.8V, per 1 ctl pin	_	1	5	μA
Supply current	Idd	VDD = 2.8V	_	150	250	μA
Switching speed	Swt	VDD = 2.8V, Vctl = 0V/1.8V			5	μS

Electrical characteristics are measured with all RF ports terminated in 50Ω .

(Ta = +25°C, VDD = 2.8V, Vctl = 0/1.8V)

Item	Symbol	Path	Condition	Min.	Тур.	Max.	Unit
VSWR	VSWR	All port in active paths	824 to 2170MHz	_	1.1	1.4	—
P0.2dB Compression input power	P0.2dB	RF4 (Ant2) –RF1, 2, 3 RF5 (Ant1) –RF1, 2, 3		33	_	_	dBm
Input IP3	IIP3	RF4 (Ant2) –RF1, 2, 3		65	_	—	dBm
	111 3	RF5 (Ant1) –RF1, 2, 3	*2, *3	65			ubiii

Electrical characteristics are measured with all RF ports terminated in 50Ω .

- *1 Pin = 27 + 27dBm, 835 + 836MHz, IIP3 = (3 × Pout IM3)/2 + Loss
- *2 Pin = 27 + 27dBm, 1950 + 1951MHz, IIP3 = (3 × Pout IM3)/2 + Loss
- *3 Measured with recommended circuit

(Ta = +25℃, \	√DD = 2.8V,	Vctl = 0/1.8V)
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Item	Symbol	State *1	Path	Condition	Min.	Тур.	Max.	Unit
				Pin= 34dBm, 824 to 960MHz	_	0.30	0.45	
			RF4 (Ant2)	Pin= 32dBm, 1710 to 1990MHz	—	0.35	0.50	
			–RF1, 2, 3	Pin= 10dBm, 2110 to 2170MHz	—	0.40	0.55	
		1-6		Pin= 10dBm, 2500 to 2690MHz	_	0.45	0.60	dB
		1-0		Pin= 34dBm, 824 to 960MHz	_	0.30	0.45	uВ
			RF5 (Ant1)	Pin= 32dBm, 1710 to 1990MHz	_	0.35	0.50	
			–RF1, 2, 3	Pin= 10dBm, 2110 to 2170MHz	—	0.40	0.55	
Insertion loss	IL			Pin= 10dBm, 2500 to 2690MHz	—	0.45	0.60	
Insention 1055				Pin= 34dBm, 824 to 960MHz	—	0.33	0.48	
			RF4 (Ant2)	Pin= 32dBm, 1710 to 1990MHz	_	0.45	0.60	
			–RF1, 2, 3	Pin= 10dBm, 2110 to 2170MHz	—	0.50	0.65	
		7-12		Pin= 10dBm, 2500 to 2690MHz	—	0.60	0.75	dB
		7-12		Pin= 34dBm, 824 to 960MHz	—	0.33	0.48	uВ
			RF5 (Ant1)	Pin= 32dBm, 1710 to 1990MHz	—	0.45	0.60	
				Pin= 10dBm, 2110 to 2170MHz	—	0.50	0.65	
				Pin= 10dBm, 2500 to 2690MHz	_	0.60	0.75	
			RF4 (Ant2) –RF1, 2, 3	Pin= 34dBm, 824 to 960MHz	25	35	_	
				Pin= 32dBm, 1710 to 1990MHz	20	28	_	
				Pin= 10dBm, 2110 to 2170MHz	20	27	_	
		1-6		Pin= 10dBm, 2500 to 2690MHz	20	25	_	
		1-0		Pin= 34dBm, 824 to 960MHz	25	36	_	dB
			RF5 (Ant1)	Pin= 32dBm, 1710 to 1990MHz	20	29	_	
			–RF1, 2, 3	Pin= 10dBm, 2110 to 2170MHz	20	28	_	
Isolation	ISO			Pin= 10dBm, 2500 to 2690MHz	20	25	_	
1501411011	150			Pin= 34dBm, 824 to 960MHz	21	—	_	
				Pin= 32dBm, 1710 to 1990MHz	16	—	_	
			–RF1, 2, 3	Pin= 10dBm, 2110 to 2170MHz	15	—	_	
		7-12		Pin= 10dBm, 2500 to 2690MHz	13	—	_	dB
		1-12		Pin= 34dBm, 824 to 960MHz	21	—	_	uD
			RF5 (Ant1)	Pin= 32dBm, 1710 to 1990MHz	16	_		
			–RF1, 2, 3	Pin= 10dBm, 2110 to 2170MHz	15	_		
				Pin= 10dBm, 2500 to 2690MHz	13	_	_	

Electrical characteristics are measured with all RF ports terminated in 50Ω .

(Ta = +25°C, V_{DD} = 2.8V, Vctl = 0/1.8V)

Item	Symbol	State	Path	Condition	Min.	Тур.	Max.	Unit
	2f0			Pin= 34dBm, 824 to 960MHz	—	-48	-36	
	3f0			FIII- 340BIII, 824 10 900MI12	_	-44	-36	
	2f0			Pin= 32dBm, 1710 to 1990MHz	—	-46	-36	
	3f0		RF4 (Ant2)		_	-47	-36	dBm
	2f0		–RF1, 2, 3	Pin= 26dBm, 1428 to 1453MHz	_	-65	-45	dbiii
	3f0				_	-65	-45	
2	2f0			Pin= 26dBm, 1920 to 1980MHz	_	-61	-45	
Harmonics	3f0	1-12		1 m 2000m, 1920 to 1900mm2	_	-64	-45	
namonica	2f0	1-12		Pin= 34dBm, 824 to 960MHz	_	-50	-36	
	3f0			1 m - 340 m, 024 to 300 m iz	_	-44	-36	
	2f0			Pin= 32dBm, 1710 to 1990MHz	—	-52	-36	
	3f0		RF5 (Ant1)	-	_	-46	-36	dBm
	2f0		–RF1, 2, 3	Pin= 26dBm, 1428 to 1453MHz	_	-65	-45	UDIII
-	3f0			FIII- 2000III, 1420 to 1433iii12	—	-65	-45	
	2f0			Pin= 26dBm, 1920 to 1980MHz	-45			
	3f0			1 III - 2000III, 1920 (0 1900WHZ	—	-65	-45	

Electrical characteristics are measured with all RF ports terminated in 50Ω .

(Ta = +25°C, VDD = 2.8V, Vctl = 0/1.8V)

Item	Symbol	State *1	Path	Condition	Min.	Тур.	Max.	Unit
				Ptx = 21.5dBm, Pjam = –15dBm, ftx = 835MHz, fjam = 45MHz, fim = 880MHz	_	-122	-105	
				Ptx = 21.5dBm, Pjam = –15dBm, ftx = 835MHz, fjam = 1715MHz, fim = 880MHz	_	-118	-105	
			–RF1, 2, 3	Ptx = 21.5dBm, Pjam = -15dBm, ftx = 1950MHz, fjam = 190MHz, fim = 2140MHz	_	-115	-105	
	IMD2	1-12		Ptx = 21.5dBm, Pjam = -15dBm, ftx = 1950MHz, fjam = 4090MHz, fim = 2140MHz	_	-106	-102	dBm
		1-12		Ptx = 21.5dBm, Pjam = –15dBm, ftx = 835MHz, fjam = 45MHz, fim = 880MHz	_	-120	-105	ubiii
			RF5 (Ant1)	Ptx = 21.5dBm, Pjam = –15dBm, ftx = 835MHz, fjam = 1715MHz, fim = 880MHz	_	-120	-105	
			–RF1, 2, 3	Ptx = 21.5dBm, Pjam = -15dBm, ftx = 1950MHz, fjam = 190MHz, fim = 2140MHz	_	-107	-103	
Intermodulation				Ptx = 21.5dBm, Pjam = -15dBm, ftx = 1950MHz, fjam = 4090MHz, fim = 2140MHz	_	-112	-105	
distortion			RF4 (Ant2)	Ptx = 21.5dBm, Pjam = –15dBm, ftx = 835MHz, fjam = 790MHz, fim = 880MHz	_	-110	-105	
				Ptx = 21.5dBm, Pjam = –15dBm, ftx = 835MHz, fjam = 2550MHz, fim = 880MHz		-113	-105	
			–RF1, 2, 3	Ptx = 21.5dBm, Pjam = -15dBm, ftx = 1950MHz, fjam = 1760MHz, fim = 2140MHz		-108	-104	
	IMD3	1-12		Ptx = 21.5dBm, Pjam = -15dBm, ftx = 1950MHz, fjam = 6040MHz, fim = 2140MHz	_	-111	-105	dBm
		1-12		Ptx = 21.5dBm, Pjam = –15dBm, ftx = 835MHz, fjam = 790MHz, fim = 880MHz		-110	-105	dDin
			RF5 (Ant1)	Ptx = 21.5dBm, Pjam = –15dBm, ftx = 835MHz, fjam = 2550MHz, fim = 880MHz		-113	-105	
			–RF1, 2, 3	Ptx = 21.5dBm, Pjam = -15dBm, ftx = 1950MHz, fjam = 1760MHz, fim = 2140MHz		-108	-104	
			Ptx = 21.5dBm, Pjam = -15dBm, ftx = 1950MHz, fjam = 6040MHz, fim = 2140MHz		-111	-105		

Electrical characteristics are measured with all RF ports terminated in $50\Omega.$ Measured with the recommended circuit.

(Ta = +25°C, V_{DD} = 2.8V, Vctl = 0/1.8V)

Item	Symbol	Path		Condition						Max.	Unit
Triple beat ratio			F	PTx at RI	=	Jammerat	Triple beat				
			PTx1 [MHz]	PTx2 [MHz]	Ant –30dBm [dBm]	product at RF [MHz]					
	TBR	BR RF4 (Ant2)	21.5	835.5	836.5	881.5	881.5 ± 1	81			
	–RF1, 2, 3 RF5 (Ant1)	21.5	1880	1881	1960	1960 ± 1	81			dBc	
		–RF1, 2, 3	13.5	1732	1733	2132	2132 ± 1	81			

Electrical characteristics are measured with all RF ports terminated in 50Ω . Measured with the recommended circuit.

(Ta = +25°C, '	VDD = 2.8V,	Vctl = 0/1.8V)
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Item	Symbol	Path		Condition		Min.	Тур.	Max.	Unit
			PTx at RF 24dBm [MHz]	Jammer at Ant –20dBm [MHz]	IM2 Product at RF [MHz]				
			836.61	1718.22	881.61	113.5		—	
Input IP2	IIP2	RF4 (Ant2) –RF1, 2, 3 RF5 (Ant1)	836.61	45	881.61	95.5		—	
			1885	3850	1965	95.5	_	_	dBm
			1885	80	1965	95.5	_	—	UDIII
		14 1, 2, 0	1732.5	3865	2132.5	95.5	_	_	
			1732.5	400	2132.5	95.5	_	_	

Electrical characteristics are measured with all RF ports terminated in 50 $\!\Omega$. Measured with the recommended circuit.

Electrical Characteristics 2

SONY

(Ta = -35 to $+90^{\circ}$ C , VDD = 2.5 to 3.2V, VctI = 0/1.8V)

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
Control current	lctl	Vctl = 1.8V, per 1 ctl pin	_	_	5	μA
Supply current	Idd		_	_	350	μA
Switching speed	Swt	Vctl = 0V/1.8V	_	_	5	μS

Electrical characteristics are measured with all RF ports terminated in 50Ω .

 $(Ta = -35 \text{ to } +90^{\circ}\text{C}, V_{DD} = 2.5 \text{ to } 3.2\text{V}, \text{Vctl} = 0/1.8\text{V})$

Item	Symbol	Path	Condition	Min.	Тур.	Max.	Unit
VSWR	VSWR	All port in active paths	824 to 2170MHz	_	1.1		—
P _{0.2dB} Compression input power	P0.2dB	RF4 (Ant2) –RF1, 2, 3 RF5 (Ant1) –RF1, 2, 3	824 to 930MHz 1710 to 1980MHz 2500 to 2690MHz	33	_	_	dBm
Input IP3	IIP3	RF4 (Ant2) –RF1, 2, 3	*1, *3	63	—		dBm
	111 3	RF5 (Ant1) –RF1, 2, 3	*2, *3	63	_		ubiii

Electrical characteristics are measured with all RF ports terminated in 50Ω .

- *1 Pin = 27 + 27dBm, 835 + 836MHz, IIP3 = (3 × Pout IM3)/2 + Loss
- *2 Pin = 27 + 27dBm, 1950 + 1951MHz, IIP3 = (3 × Pout IM3)/2 + Loss
- *3 Measured with recommended circuit

Item	Symbol	State	Path	Condition	Min.	Тур.	Max.	Unit
			RF4 (Ant2)	Pin= 34dBm, 824 to 960MHz	_	—	0.55	
				Pin= 32dBm, 1710 to 1990MHz	_	—	0.60	
			–RF1, 2, 3	Pin= 10dBm, 2110 to 2170MHz	_	—	0.65	
				Pin= 10dBm, 2500 to 2690MHz	_	—	0.70	
		1-6		Pin= 34dBm, 824 to 960MHz	_	—	0.55	dB
			RF5 (Ant1)	Pin= 32dBm, 1710 to 1990MHz		—	0.60	
			–RF1, 2, 3	Pin= 10dBm, 2110 to 2170MHz	_	—	0.65	
Insertion loss	IL			Pin= 10dBm, 2500 to 2690MHz		—	0.70	
				Pin= 34dBm, 824 to 960MHz	_	—	0.58	
				Pin= 32dBm, 1710 to 1990MHz	_	—	0.70	
			–RF1, 2, 3	Pin= 10dBm, 2110 to 2170MHz	_	—	0.75	
		7-12		Pin= 10dBm, 2500 to 2690MHz	_	—	0.85	- dB
				Pin= 34dBm, 824 to 960MHz	_	—	0.58	
			RF5 (Ant1) –RF1, 2, 3	Pin= 32dBm, 1710 to 1990MHz	_	—	0.70	
				Pin= 10dBm, 2110 to 2170MHz	_	—	0.75	
				Pin= 10dBm, 2500 to 2690MHz	_	—	0.85	
		1-6		Pin= 34dBm, 824 to 960MHz	25	—	_	- dB
				Pin= 32dBm, 1710 to 1990MHz	20	—	_	
				Pin= 10dBm, 2110 to 2170MHz	20	—	_	
				Pin= 10dBm, 2500 to 2690MHz	20	—	_	
			RF5 (Ant1)	Pin= 34dBm, 824 to 960MHz	25	—	_	
				Pin= 32dBm, 1710 to 1990MHz	20	—	_	
			–RF1, 2, 3	Pin= 10dBm, 2110 to 2170MHz	20	—	_	
Isolation	ISO			Pin= 10dBm, 2500 to 2690MHz	20	—	_	
Isolation	150			Pin= 34dBm, 824 to 960MHz	20	—	_	
			RF4 (Ant2)	Pin= 32dBm, 1710 to 1990MHz	15	—	_	
			–RF1, 2, 3	Pin= 10dBm, 2110 to 2170MHz	14	—	_	
		7-12		Pin= 10dBm, 2500 to 2690MHz	12	_	_	
		1-12		Pin= 34dBm, 824 to 960MHz	20	—	_	dB
			RF5 (Ant1)	Pin= 32dBm, 1710 to 1990MHz	15	—		
			–RF1, 2, 3	Pin= 10dBm, 2110 to 2170MHz	14	_	_	
				Pin= 10dBm, 2500 to 2690MHz	12			1

Electrical characteristics are measured with all RF ports terminated in 50Ω .

 $(Ta = -35 \text{ to } +90^{\circ}\text{C}, V_{DD} = 2.5 \text{ to } 3.2\text{V}, \text{Vctl} = 0/1.8\text{V})$

Item	Symbol	State	Path	Condition	Min.	Тур.	Max.	Unit
	2f0				_	_	-36	
	3f0			Pin= 34dBm, 824 to 960MHz	_	_	-36	
	2f0			Pin= 32dBm, 1710 to 1990MHz			-36	
	3f0		RF4 (Ant2)	-	_	_	-36	dBm
	2f0		–RF1, 2, 3	Pin= 26dBm, 1428 to 1453MHz	_	_	-45	ubiii
	3f0			PIII- 2006III, 1420 to 1455WIFZ	_	-	-45	-
	2f0		12 RF5 (Ant1) –RF1, 2, 3	Pin= 26dBm, 1920 to 1980MHz			-45	
Harmonics	3f0	1-12			_	_	-45	
Tiarrionics	2f0	1-12		Pin= 34dBm, 824 to 960MHz Pin= 32dBm, 1710 to 1990MHz	_	-	-36	
	3f0				_	_	-36	
	2f0				_	_	-36	
	3f0				_	-	-36	dBm
	2f0				_	_	-45	ubiii
	3f0		Pin= 26dBm, 1428 to 1453MHz	_	_	-45		
	2f0		Din- 26dBm 1020 to 1080MHz	—	—	-45		
	3f0			Pin= 26dBm, 1920 to 1980MHz		_	-45	

Electrical characteristics are measured with all RF ports terminated in 50Ω .

(Ta = −35 to +90°C	, VDD = 2.5 to 3.2V, Vctl = 0/1.8V)
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Item	Symbol	State *1	Path	Condition	Min.	Тур.	Max.	Unit
			RF4 (Ant2) –RF1, 2, 3	Ptx = 21.5dBm, Pjam = –15dBm, ftx = 835MHz, fjam = 45MHz, fim = 880MHz	_	_	-102	
				Ptx = 21.5dBm, Pjam = –15dBm, ftx = 835MHz, fjam = 1715MHz, fim = 880MHz	_	_	-102	
				Ptx = 21.5dBm, Pjam = -15dBm, ftx = 1950MHz, fjam = 190MHz, fim = 2140MHz		_	-102	
	IMD2	1-12		Ptx = 21.5dBm, Pjam = -15dBm, ftx = 1950MHz, fjam = 4090MHz, fim = 2140MHz	_	_	-99	dBm
		1-12		Ptx = 21.5dBm, Pjam = –15dBm, ftx = 835MHz, fjam = 45MHz, fim = 880MHz	_	_	-102	dDin
			RF5 (Ant1)	Ptx = 21.5dBm, Pjam = –15dBm, ftx = 835MHz, fjam = 1715MHz, fim = 880MHz	_	_	-102	-
Intermodulation				Ptx = 21.5dBm, Pjam = -15dBm, ftx = 1950MHz, fjam = 190MHz, fim = 2140MHz	_	_	-100	
				Ptx = 21.5dBm, Pjam = -15dBm, ftx = 1950MHz, fjam = 4090MHz, fim = 2140MHz	_	_	-102	
distortion	IMD3 1-12	1.40	RF4 (Ant2) -RF1, 2, 3	Ptx = 21.5dBm, Pjam = –15dBm, ftx = 835MHz, fjam = 790MHz, fim = 880MHz	_	_	-102	- dBm
				Ptx = 21.5dBm, Pjam = -15dBm, ftx = 835MHz, fjam = 2550MHz, fim = 880MHz	_	_	-102	
				Ptx = 21.5dBm, Pjam = -15dBm, ftx = 1950MHz, fjam = 1760MHz, fim = 2140MHz	_	_	-101	
				Ptx = 21.5dBm, Pjam = -15dBm, ftx = 1950MHz, fjam = 6040MHz, fim = 2140MHz	_	_	-102	
		1-12		Ptx = 21.5dBm, Pjam = –15dBm, ftx = 835MHz, fjam = 790MHz, fim = 880MHz	_	_	-102	
			RF5 (Ant1)	Ptx = 21.5dBm, Pjam = –15dBm, ftx = 835MHz, fjam = 2550MHz, fim = 880MHz	_	_	-102	
				Ptx = 21.5dBm, Pjam = -15dBm, ftx = 1950MHz, fjam = 1760MHz, fim = 2140MHz			-101	
				Ptx = 21.5dBm, Pjam = –15dBm, ftx = 1950MHz, fjam = 6040MHz, fim = 2140MHz	_	_	-102	

Electrical characteristics are measured with all RF ports terminated in $50\Omega.$ Measured with the recommended circuit.

Recommended Circuit



Note) 1. No DC blocking capacitors are required on all RF ports.

- 2. The DC levels of all RF ports are GND.
- 3. L1 (27nH) and C1 (12pF) are recommended on antenna port for ESD protection.
- 4. Cbypass (100pF) is recommended on VDD for DC line filtering.

PCB Layout Template

XQFN-22P-01 Macro for MMIC (Reference)

Specification

- PKG size: 3.3mm × 2.4mm t0.35mm
- Terminal pitch: 0.4mm
- Terminal length: 0.3mm
- Mask thickness: 0.11mm







Package Outline

(Unit: mm)

22PIN XQFN (PLASTIC)



TERMINAL SECTION

Note:Cutting burr of lead are 0.05mm MAX.

X Q F N - 2 2 P - 0 1

PACKAGE STRUCTURE

PACKAGE MATERIAL	EPOXY RESIN
LEAD TREATMENT	SOLDER PLATING
LEAD MATERIAL	COPPER ALLOY
PACKAGE MASS	0.019

AP-4000-22008S Rev. 0

SONY CODE

JEITA CODE JEDEC CODE

LEAD PLATING SPECIFICATIONS

ITEM	SPEC.
LEAD MATERIAL	COPPER ALLOY
SOLDER COMPOSITION	Sn-Bi Bi:1-4wt%
PLATING THICKNESS	5-18µm

Marking



MARKING C: M3544

注1) B部はロット番号(Max3文字で通し記号)を配置する。	
(規定文字数未満につき省略は省略規定に従う。	
製造年は下記2進法ビット方式により表示する。)	d b
a部年コード(2進法ビット方式の1ビット目を表示)を配置する。	
	t a
	DETAIL B
 注2) C部は製品名(Ma×5文字)を配置する。	
<u>注3) マーク深さは,MaxO.O5mmの事。</u>	
< INSTRUCTIONS >	
1) LOT NO. (MAX 3 CHARACTERS : SERIAL CODE) IN SECTION B.	
(FOLLOW RULES FOR ABBREVIATIONS.	
MANUFACTURING YEAR IS DISPLAYED BY FOLLOWING BYNARY BIT SYSTEM.)	
A YEAR CODE (THE 1ST BIT OF A BINARY SYSTEM BIT SYSTEM IS DISPLAYED IN 1 DOT) IN SECTION a.	
A YEAR CODE (THE 2ND BIT OF A BINARY SYSTEM BIT SYSTEM IS DISPLAYED IN 1 DOT) IN SECTION b.	
A YEAR CODE (THE 3RD BIT OF A BINARY SYSTEM BIT SYSTEM IS DISPLAYED IN 1 DOT) IN SECTION c.	
A YEAR CODE (THE 4TH BIT OF A BINARY SYSTEM BIT SYSTEM IS DISPLAYED IN 1 DOT) IN SECTION d.	
2) TYPE NO. (MAX 5 CHARACTERS) IN SECTION C.	
(FOR MORE THAN 5 CHARACTERS FOLLOW RULES FOR ABBREVIATIONS.)	
3) MARK DEPTH MAX 0.05 mm.	